Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A composition for removing etch and/or ash residue or contaminants from a semiconductor substrate comprising:
   (A) from ~~30~~ 45 to 90 wt% of a water soluble organic solvent,
   (B) from 3 to 10 wt% of a sulfonic acid or its corresponding salt, and
   (C) from 5 to 50 wt% water.
2. (Original) The composition as claimed in claim 1, further comprising a corrosion inhibitor.
3. (Original) The composition as claimed in claim 1, wherein the water soluble organic solvent is monoethanolamine, N-methylethanolamine, dimethylsulfoxide, dimethylacetamide or mixtures thereof.
4. (Original) The composition as claimed in claim 1, wherein the sulfonic acid or its corresponding salt is p-toluene sulfonic acid, 1,5-naphthalene disulfonic acid, 4-ethylbenzene sulfonic acid, dodecylbenzene sulfonic acid or mixtures thereof.
5. (Original) The composition as claimed in claim 2, wherein the corrosion inhibitor is gallic acid, catechol, benzotriazole, benzoic acid, malonic acid, ammonium malonate or mixtures thereof.

Canceled claims 6-7

8. (Withdrawn) A method of removing photoresist, etch and/or ash residue, or contaminants from a semiconductor substrate, comprising; contacting the semiconductor substrate with a composition, comprising:
   a. a water soluble organic solvent,

b. a sulfonic acid or its corresponding salt, and

c. water;

for a period of time sufficient to remove the photoresist, etch and/or ash residue or contaminants.

9. (Withdrawn) The method as claimed in claim 8, wherein the composition further comprises a corrosion inhibitor.

10. (Withdrawn) The method as claimed in claim 8, wherein the water soluble organic solvent is monoethanolamine, N-methylethanolamine, dimethylsulfoxide, dimethylacetamide or mixtures thereof.

11. (Withdrawn) The method as claimed in claim 8, wherein the sulfonic acid or its corresponding salt is p-toluene sulfonic acid, 1,5-naphthalene disulfonic acid, 4-ethylbenzene sulfonic acid, dodecylbenzene sulfonic acid or mixtures thereof,

12. (Withdrawn) The method as claimed in claim 9, wherein the corrosion inhibitor is gallic acid, catechol, benzotriazole, benzoic acid, mallonic acid, ammonium malonate or mixtures thereof.

13. (Currently Amended) A composition for removing etch and/or ash residue or contaminants from a semiconductor substrate comprising:

(A) from ~~30~~ 45 to 90 wt% of a water soluble organic solvent,

(B) from 3 to 10 wt% of a sulfonic acid or its corresponding salt,

(C) from 5 to 50 wt% water, and

(D) optionally from 0.1 to 15 wt% of a corrosion inhibitor.

14. (Currently Amended) A composition for removing etch and/or ash residue or contaminants from a semiconductor substrate comprising:

(A) from ~~30~~ 45 to 90 wt% of a water soluble organic solvent,

(B) from 1 to 20 wt% of a sulfonic acid or its corresponding salt,

(C) from 5 to 50 wt% water, and

(D) from 0.1 to 20 wt% of a corrosion inhibitor.

15. (New) The composition of claim 13 wherein component (B) comprises an alkylbenzene sulfonate having less than 9 carbon atoms.

16. (New) The composition of claim 13 wherein amount of component (A) ranges from 50 to 90 wt%.

17. (New) The composition of claim 16 wherein amount of component (A) ranges from 60 to 90 wt%.

18. (New) The composition of claim 14 wherein component (B) comprises a alkylbenzene sulfonate having less than 9 carbon atoms.

19. (New) The composition of claim 14 wherein amount of component (A) ranges from 50 to 90 wt%.

20. (New) The composition of claim 19 wherein amount of component (A) ranges from 60 to 90 wt%.